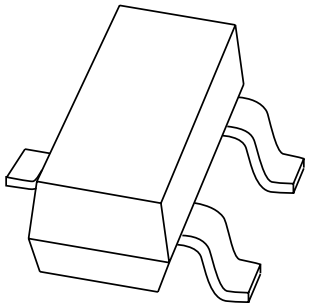
DATA SHEET



BC856; BC857; BC858
PNP general purpose transistors

Product specification
Supersedes data of 1999 Apr 12

2002 Feb 04

Philips
Semiconductors

PHILIPS

PNP general purpose transistors BC856; BC857; BC858

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complements: BC846, BC847 and BC848.

MARKING

TYPE NUMBER	MARKING CODE(1)
BC856	3D*
BC856A	3A*
BC856B	3B*
BC857	3H*
BC857A	3E*
BC857B	3F*
BC857C	3G*
BC858B	3K*

Note

1. * = -: made in Hong Kong.
   * = t: made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

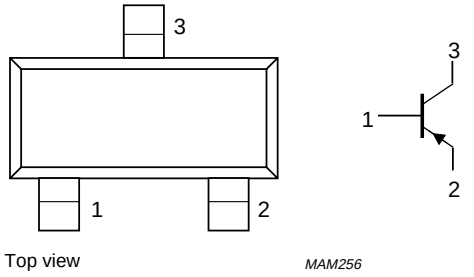


Fig.1 Simplified outline (SOT23) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC856		–	–80	V
	BC857		–	–50	V
	BC858		–	–30	V
V_{CEO}	collector-emitter voltage	open base			
	BC856		–	–65	V
	BC857		–	–45	V
	BC858		–	–30	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air; note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

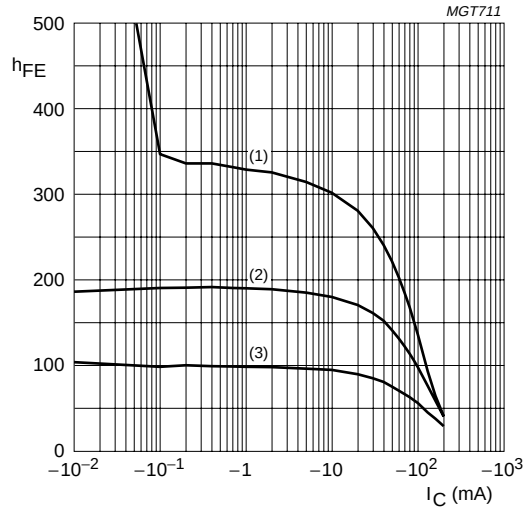
CHARACTERISTICS

T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = –30 V; I_E = 0	–	–1	–15	nA
		V_{CB} = –30 V; I_E = 0; T_j = 150 °C	–	–	–4	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0	–	–	–100	nA
h_{FE}	DC current gain	I_C = –2 mA; V_{CE} = –5 V				
	BC856		125	–	475	
	BC857		125	–	800	
	BC856A; BC857A		125	–	250	
	BC856B; BC857B; BC858B		220	–	475	
	BC857C		420	–	800	
V_{CEsat}	collector-emitter saturation voltage	I_C = –10 mA; I_B = –0.5 mA	–	–75	–300	mV
		I_C = –100 mA; I_B = –5 mA; note 1	–	–250	–650	mV
V_{BEsat}	base-emitter saturation voltage	I_C = –10 mA; I_B = –0.5 mA	–	–700	–	mV
		I_C = –100 mA; I_B = –5 mA; note 1	–	–850	–	mV
V_{BE}	base-emitter voltage	I_C = –2 mA; V_{CE} = –5 V	–600	–650	–750	mV
		I_C = –10 mA; V_{CE} = –5 V	–	–	–820	mV
C_c	collector capacitance	V_{CB} = –10 V; I_E = I_e = 0; f = 1 MHz	–	4.5	–	pF
f_T	transition frequency	V_{CE} = –5 V; I_C = –10 mA; f = 100 MHz	100	–	–	MHz
F	noise figure	I_C = –200 µA; V_{CE} = –5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	–	2	10	dB

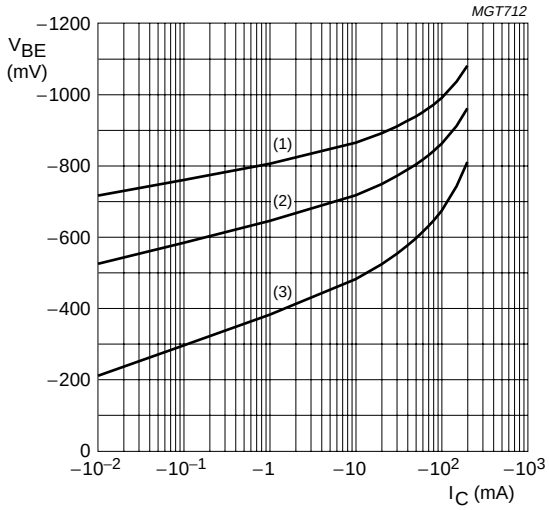
Note

1. Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.



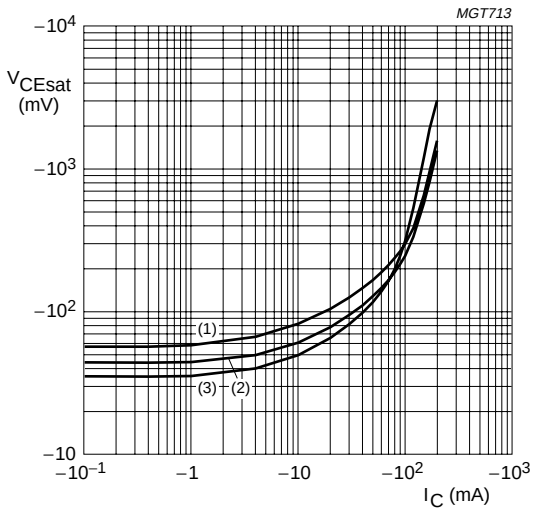
BC857A; V_{CE} = –5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = –55 °C.

Fig.2 DC current gain as a function of collector current; typical values.



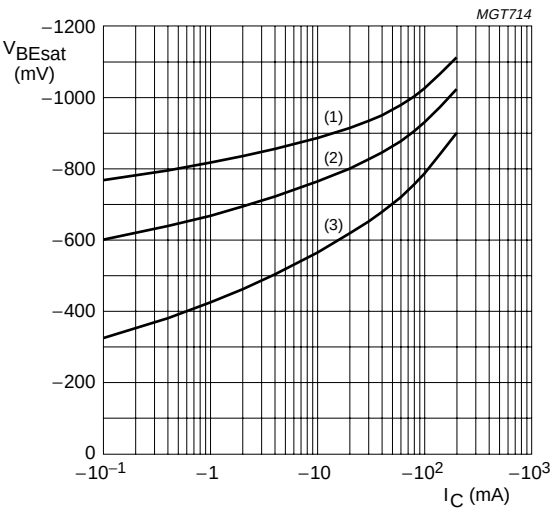
BC857A; V_{CE} = –5 V.
(1) T_{amb} = –55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



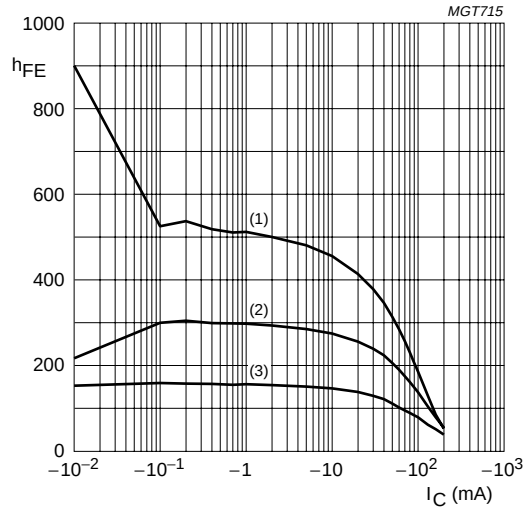
BC857A; I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = –55 °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



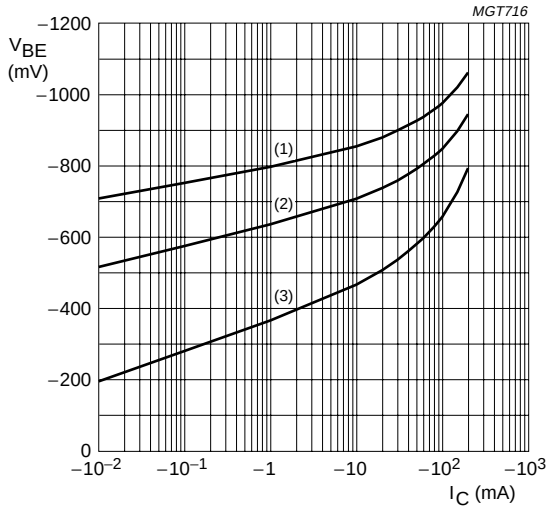
BC857A; I_C/I_B = 20.
(1) T_{amb} = –55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.



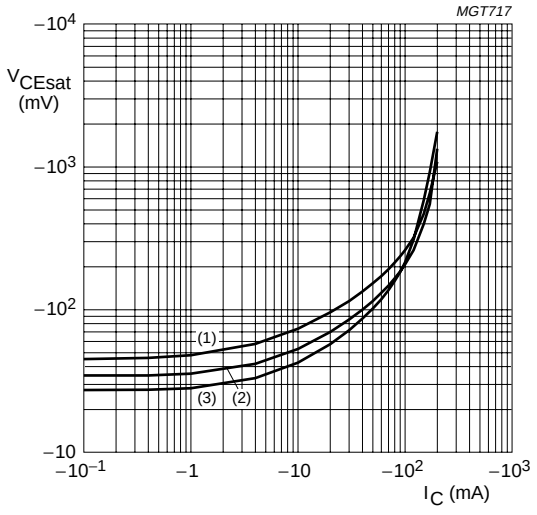
BC857B; V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.6 DC current gain as a function of collector current; typical values.



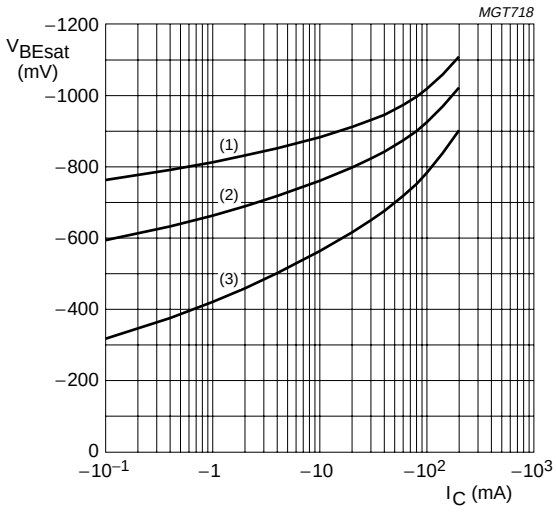
BC857B; V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.



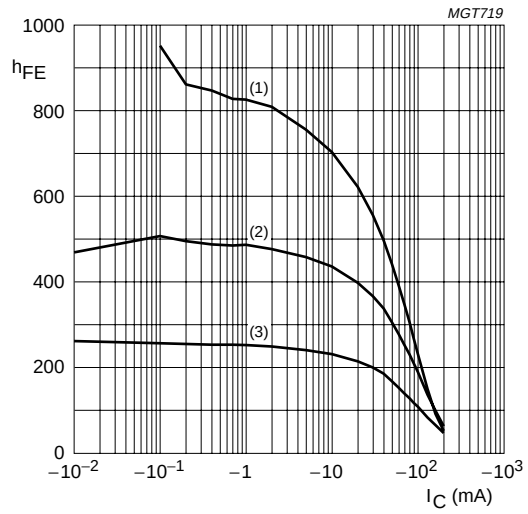
BC857B; I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



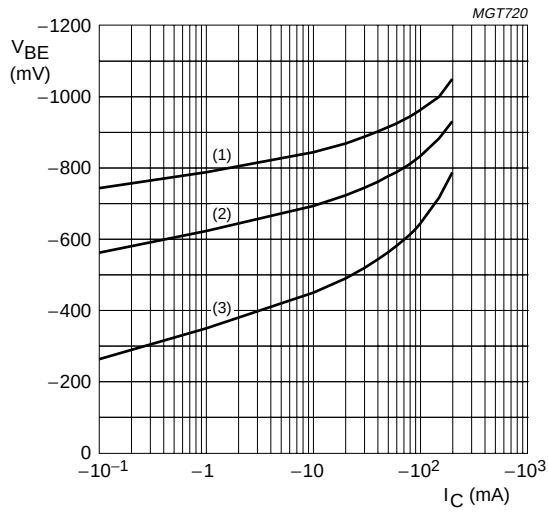
BC857B; I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.



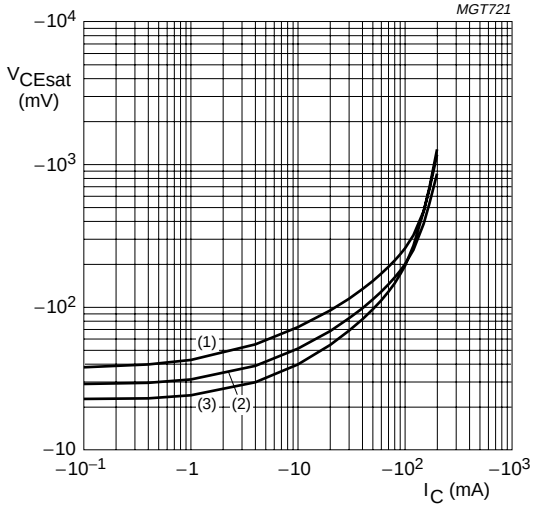
BC857C; V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.10 DC current gain as a function of collector current; typical values.



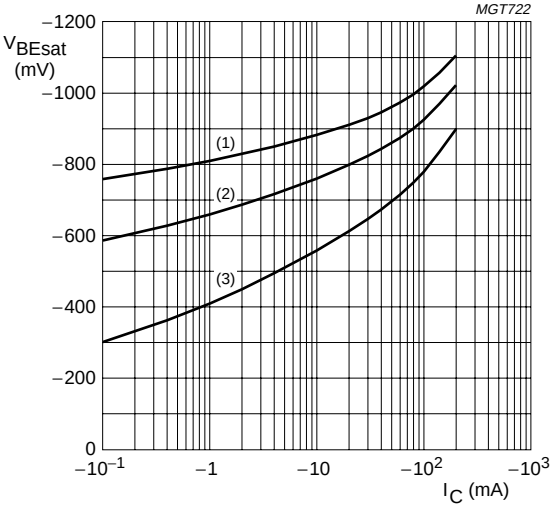
BC857C; V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.11 Base-emitter voltage as a function of collector current; typical values.



BC857C; I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.

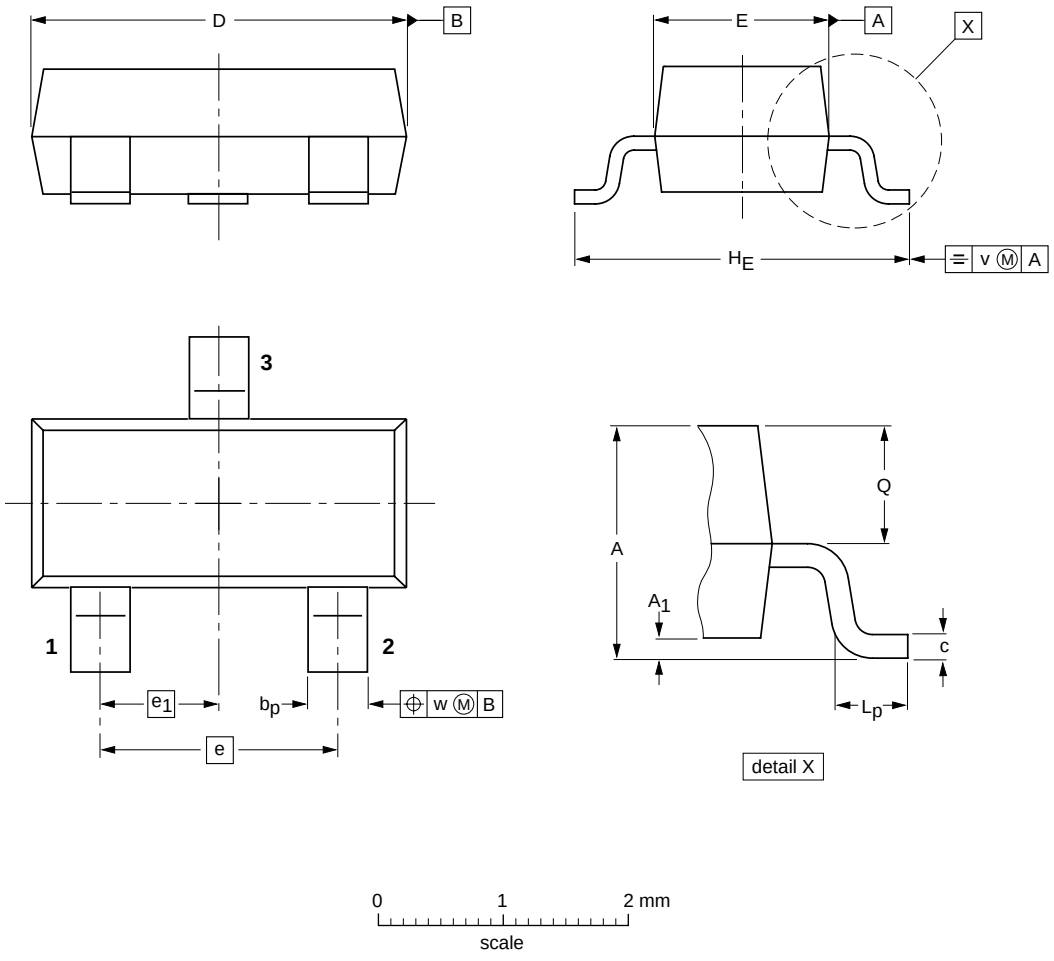


BC857C; I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				~~97-02-28~~ 99-09-13

BC856; BC857; BC858

65 V, 100 mA PNP general-purpose transistors

Rev. 7 — 16 April 2018 Product data sheet

1 Product profile

1.1 General description

PNP general-purpose transistors in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		NPN complement
	Nexperia	JEDEC	
BC856	SOT23	TO-236AB	BC846
BC856A			BC846A
BC856B			BC846B
BC857			BC847
BC857A			BC847A
BC857B			BC847B
BC857C			BC847C
BC858B			BC848B

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 65 V)
- AEC-Q101 qualified

1.3 Applications

- General-purpose switching and amplification

1.4 Quick reference data

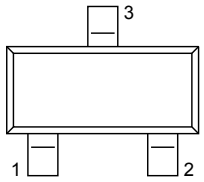
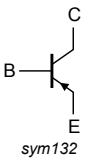
Table 2. Quick reference data

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base					
	BC856			-	-	-65	V
	BC857			-	-	-45	V
	BC858B			-	-	-30	V
I_C	collector current			-	-	-100	mA
I_{CM}	peak collector current			-	-	-200	mA
h_{FE}	DC current gain	V_{CE} = -5 V; I_C = -2 mA					
	BC856			125	-	475	-
	BC857			125	-	800	-
	BC856A; BC857A			125	-	250	-
	BC856; BC857B; BC858B			220	-	475	-
	BC857C			420	-	800	-

2 Pinning information

Table 3. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	E	emitter		
3	C	collector		

3 Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BC856	TO-236AB	Plastic surface-mounted package; 3 leads	SOT23
BC856A			
BC856B			
BC857			
BC857A			
BC857B			
BC857C			
BC858B			

4 Marking

Table 5. Marking codes

Type number		Marking code
BC856	[1]	3D%
BC856A	[1]	3A%
BC856B	[1]	3B%
BC857	[1]	3H%
BC857A	[1]	3E%
BC857B	[1]	3F%
BC857C	[1]	3G%
BC858B	[1]	3K%

[1] % = placeholder for manufacturing site code

5 Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter				
	BC856			-	-80	V
	BC857			-	-50	V
	BC858B			-	-30	V
V_{CEO}	collector-emitter voltage	open base				
	BC856			-	-65	V
	BC857			-	-45	V
	BC858B			-	-30	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I_C	collector current			-	-100	mA
I_{CM}	peak collector current			-	-200	mA
I_{BM}	peak base current			-	-200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	250	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-65	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.

6 Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.

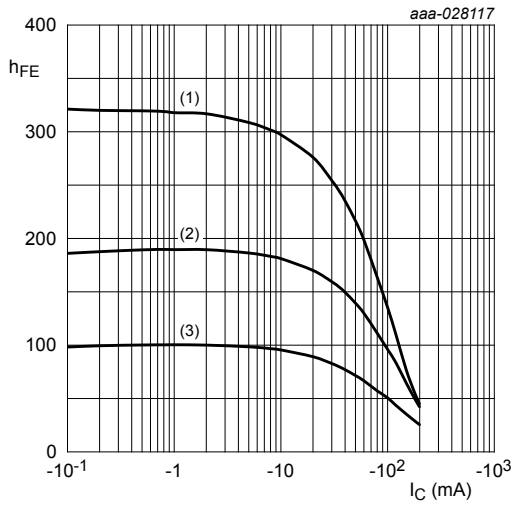
7 Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

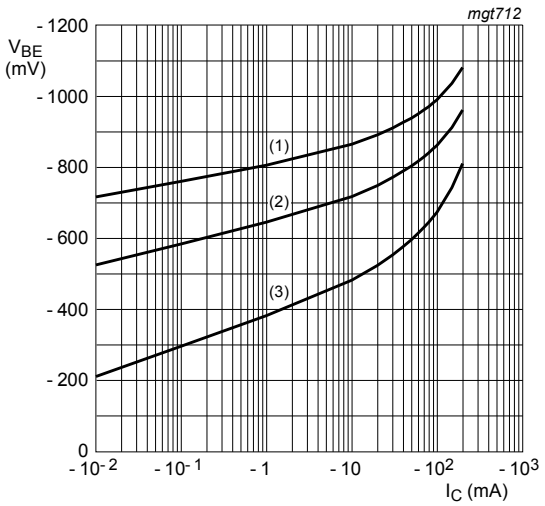
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = -30 V; I_E = 0		-	-1	-15	nA
		V_{CB} = -30 V; I_E = 0; T_j = 150 °C		-	-	-4	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I_C = 0		-	-	-100	nA
h_{FE}	DC current gain						
	BC856	V_{CE} = -5 V; I_C = -2 mA		125	-	475	
	BC857			125	-	800	
	BC856A; BC857A			125	-	250	
	BC856B; BC857B; BC858B			220	-	475	
	BC857C			420	-	800	
V_{CEsat}	collector-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA		-	-75	-300	mV
		I_C = -100 mA; I_B = -5 mA	[1]	-	-250	-650	mV
V_{BEsat}	base-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA		-	-700	-	mV
		I_C = -100 mA; I_B = -5 mA	[1]	-	-850	-	mV
V_{BE}	base-emitter voltage	V_{CE} = -5 V; I_C = -2 mA		-600	-650	-750	mV
		V_{CE} = -5 V; I_C = -10 mA		-	-	-820	mV
f_T	transition frequency	V_{CE} = -5 V; I_C = -10 mA; f = 100 MHz		100	-	-	MHz
C_c	collector capacitance	V_{CB} = -10 V; I_E = i_e = 0 A; f = 1 MHz		-	4.5	-	pF
F	noise figure	I_C = -200 µA; V_{CE} = -5 V; R_S = 2 kΩ; f = 1 kHz; B = 200Hz		-	2	10	dB

[1] pulsed; $t_p \leq 300$ µs; $\delta \leq 0.02$



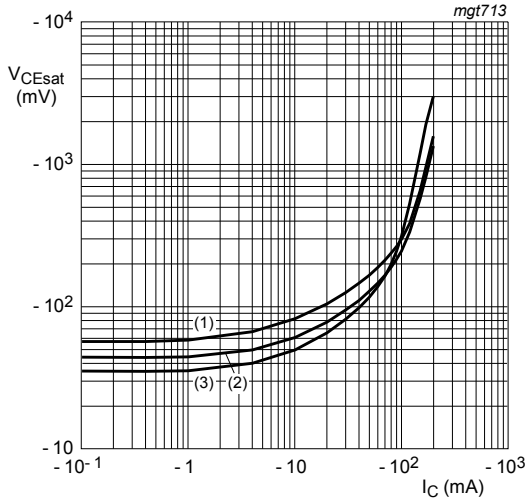
V_{CE} = -5 V
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Figure 1. BC856A; BC857A: DC current gain as a function of collector current; typical values



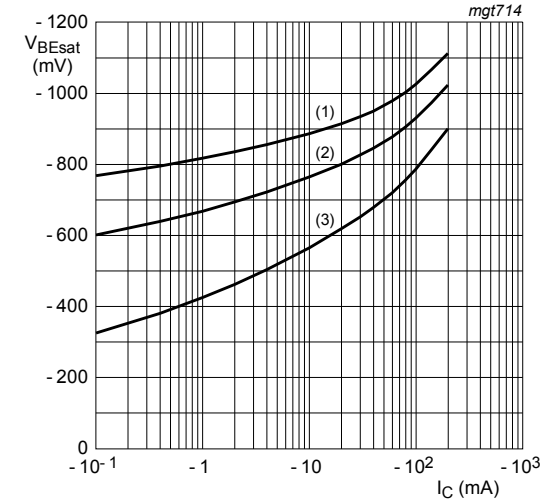
V_{CE} = -5 V
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Figure 2. BC856A; BC857A: Base-emitter voltage as a function of collector current; typical values



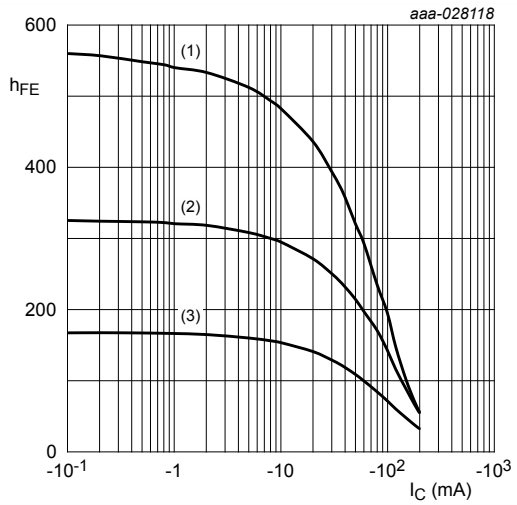
I_C/I_B = 20
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Figure 3. BC856A; BC857A: Collector-emitter saturation voltage as a function of collector current; typical values



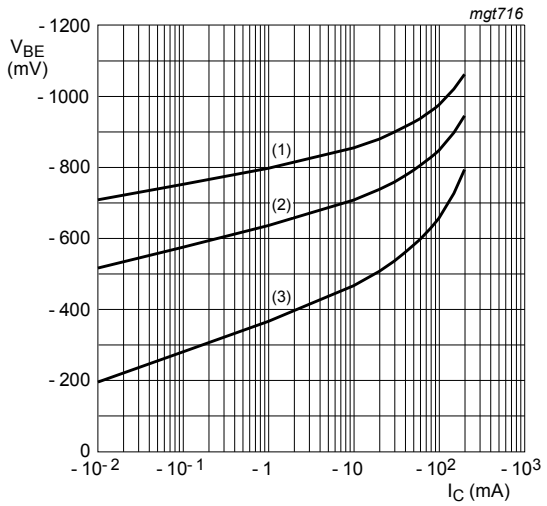
I_C/I_B = 20
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Figure 4. BC856A; BC857A: Base-emitter saturation voltage as a function of collector current; typical values



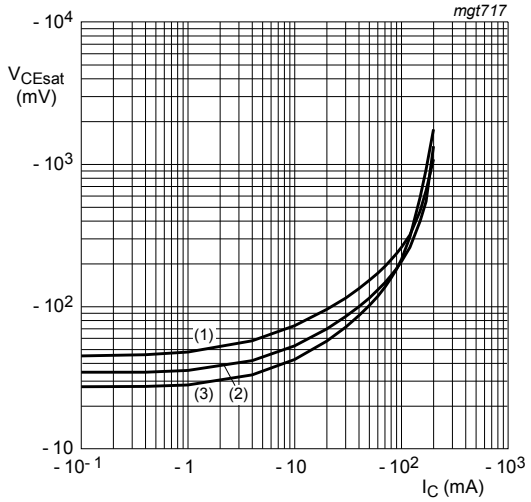
V_{CE} = -5 V
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Figure 5. BC856B; BC857B; BC858B: DC current gain as a function of collector current; typical values



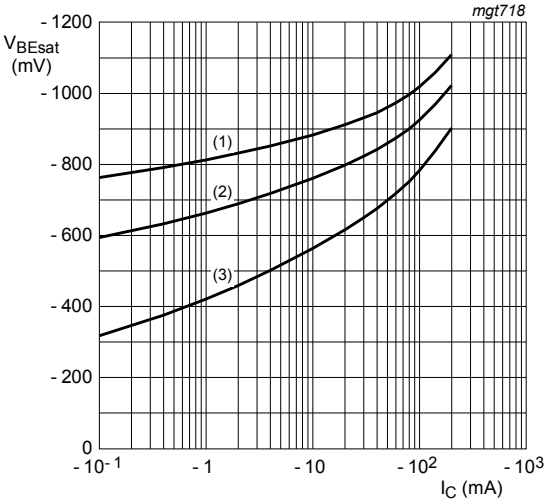
V_{CE} = -5 V
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Figure 6. BC856B; BC857B; BC858B: Base-emitter voltage as a function of collector current; typical values



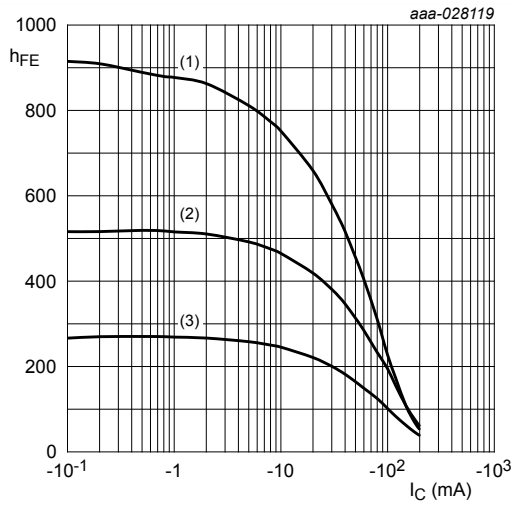
I_C/I_B = 20
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Figure 7. BC856B; BC857B; BC858B: Collector-emitter saturation voltage as a function of collector current; typical values



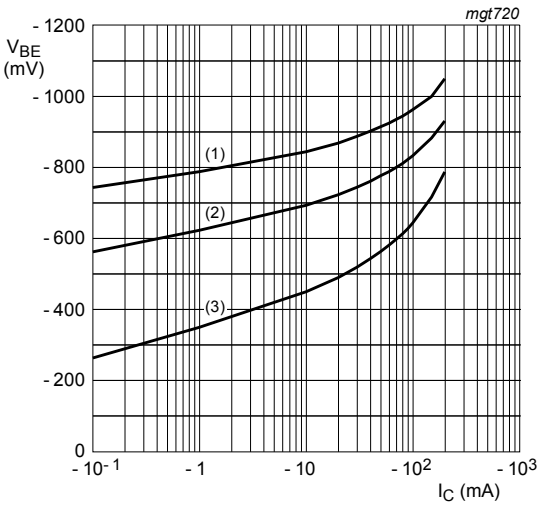
I_C/I_B = 20
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Figure 8. BC856B; BC857B; BC858B: Base-emitter saturation voltage as a function of collector current; typical values



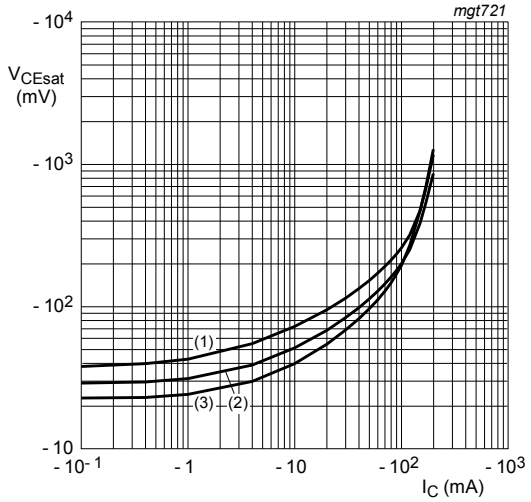
V_{CE} = -5 V
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Figure 9. BC857C: DC current gain as a function of collector current; typical values



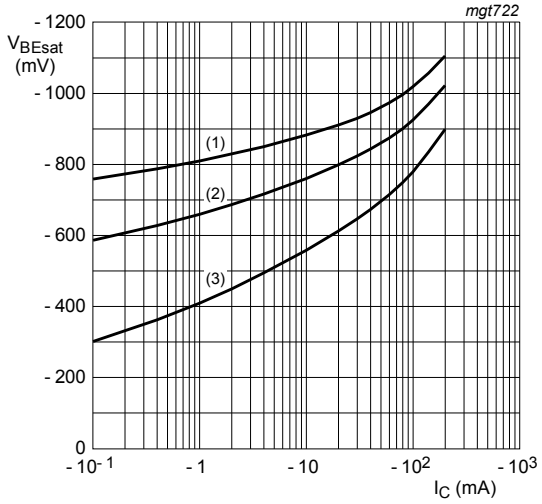
V_{CE} = -5 V
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Figure 10. BC857C: Base-emitter voltage as a function of collector current; typical values



I_C/I_B = 20
(1) T_{amb} = 150 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Figure 11. BC857C: Collector-emitter saturation voltage as a function of collector current; typical values



I_C/I_B = 20
(1) T_{amb} = -55 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = 150 °C

Figure 12. BC857C: Base-emitter saturation voltage as a function of collector current; typical values

8 Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9 Package outline

Table 9. Package outline

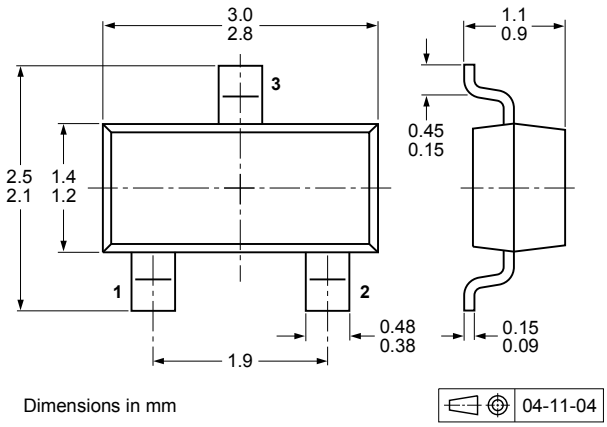


Figure 13. Package outline SOT23 (TO-236AB)

10 Soldering

Table 10. Soldering

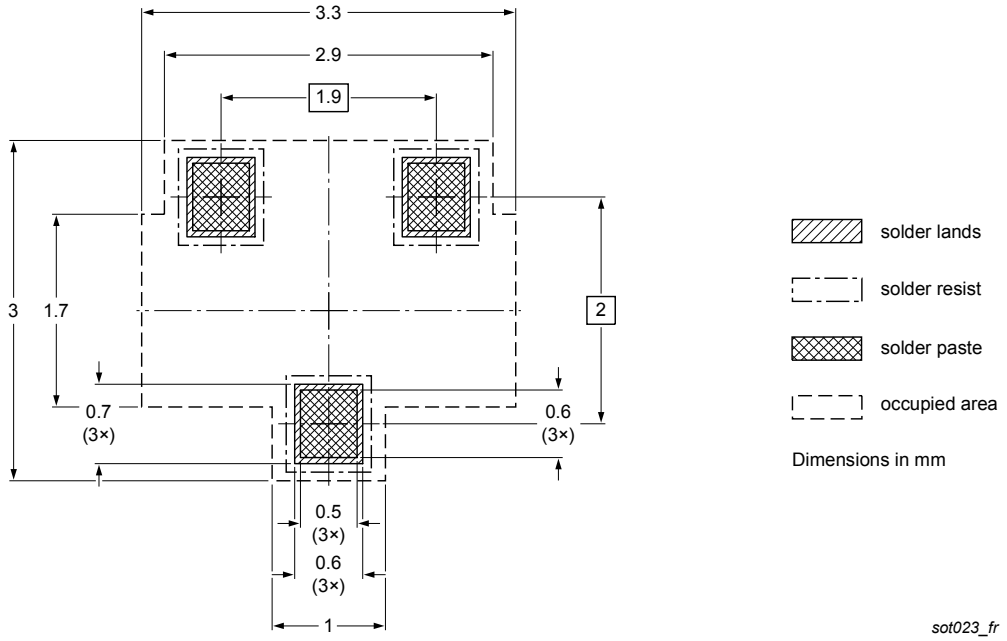


Figure 14. Reflow soldering footprint for SOT23 (TO-236AB)

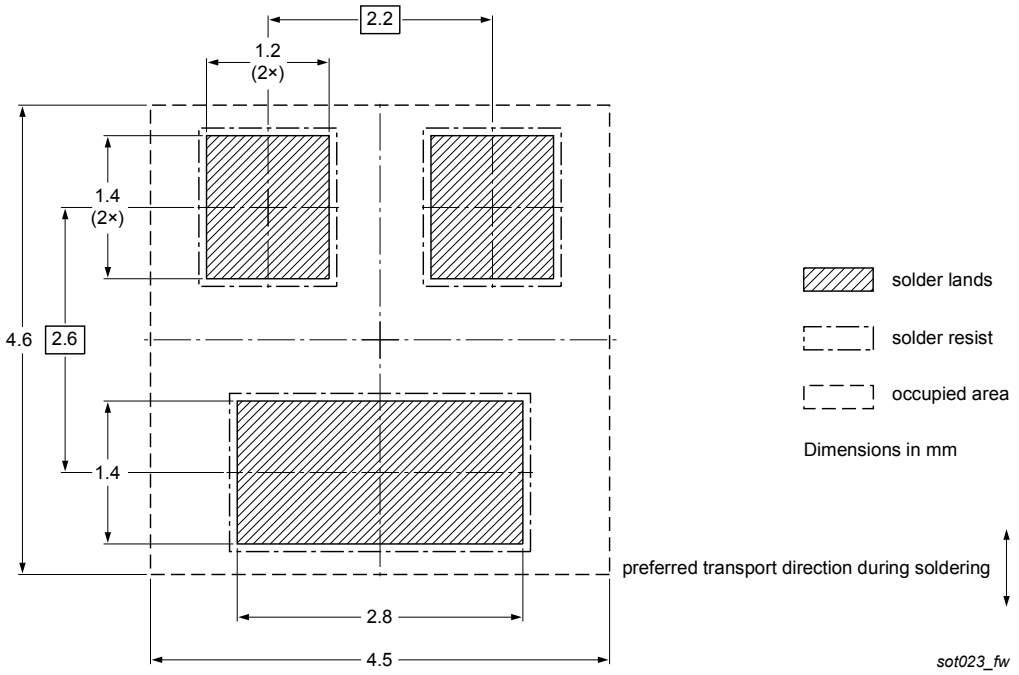
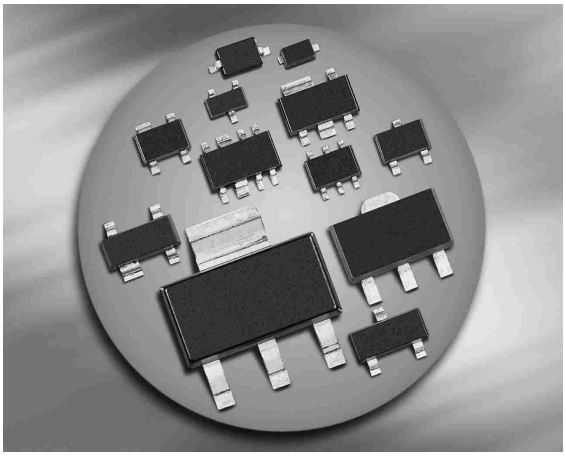


Figure 15. Wave soldering footprint for SOT23 (TO-236AB)

PNP Silicon AF Transistor

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 hz and 15 kHz
- Complementary types:
  BC847...-BC850... (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101[1)]



AEC Qualified RoHS

[1]BC857BL3 is not qualified according AEC Q101

Type	Marking	Pin Configuration						Package
BC857A	3Es	1=B	2=E	3=C	-	-	-	SOT23
BC857B	3Fs	1=B	2=E	3=C	-	-	-	SOT23
BC857BL3*	3F	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC857BW	3Fs	1=B	2=E	3=C	-	-	-	SOT323
BC857C	3Gs	1=B	2=E	3=C	-	-	-	SOT23
BC857CW	3Gs	1=B	2=E	3=C	-	-	-	SOT323
BC858A	3Js	1=B	2=E	3=C	-	-	-	SOT23
BC858B	3Ks	1=B	2=E	3=C	-	-	-	SOT23
BC858BW	3Ks	1=B	2=E	3=C	-	-	-	SOT323
BC858C	3Ls	1=B	2=E	3=C	-	-	-	SOT23
BC858CW	3Ls	1=B	2=E	3=C	-	-	-	SOT323
BC859C	4Cs	1=B	2=E	3=C	-	-	-	SOT23
BC860B	4Fs	1=B	2=E	3=C	-	-	-	SOT23
BC860BW	4Fs	1=B	2=E	3=C	-	-	-	SOT323
BC860CW	4Gs	1=B	2=E	3=C	-	-	-	SOT323

* Not qualified according AEC Q101

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
BC857..., BC860...		45	
BC858..., BC859...		30	
Collector-base voltage	V_{CBO}		
BC857..., BC860...		50	
BC858..., BC859...		30	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	100	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	200	
Total power dissipation	P_{tot}		mW
$T_S \leq 71$ °C, BC857-BC860		330	
$T_S \leq 135$ °C, BC857BL3		250	
$T_S \leq 124$ °C, BC857W-BC860W		250	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}		K/W
BC857-BC860		≤ 240	
BC857BL3		≤ 60	
BC857W-BC860W		≤ 105	

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$V_{(BR)CEO}$				V
I_C = 10 mA, I_B = 0 , BC857..., BC860...		45	-	-	
I_C = 10 mA, I_B = 0 , BC858..., BC859...		30	-	-	
Collector-base breakdown voltage	$V_{(BR)CBO}$				
I_C = 10 µA, I_E = 0 , BC857..., BC860...		50	-	-	
I_C = 10 µA, I_E = 0 , BC858..., BC859...		30	-	-	
Emitter-base breakdown voltage	$V_{(BR)EBO}$	5	-	-	
I_E = 1 µA, I_C = 0					
Collector-base cutoff current	I_{CBO}				µA
V_{CB} = 45 V, I_E = 0		-	-	0.015	
V_{CB} = 30 V, I_E = 0 , T_A = 150 °C		-	-	5	
DC current gain[1)]	h_{FE}				-
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.A		-	140	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.B		-	250	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.C		-	480	-	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.A		125	180	250	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.B		220	290	475	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.C		420	520	800	
Collector-emitter saturation voltage[1)]	V_{CEsat}				mV
I_C = 10 mA, I_B = 0.5 mA		-	75	300	
I_C = 100 mA, I_B = 5 mA		-	250	650	
Base emitter saturation voltage[1)]	V_{BEsat}				
I_C = 10 mA, I_B = 0.5 mA		-	700	-	
I_C = 100 mA, I_B = 5 mA		-	850	-	
Base-emitter voltage[1)]	$V_{BE(ON)}$				
I_C = 2 mA, V_{CE} = 5 V		600	650	750	
I_C = 10 mA, V_{CE} = 5 V		-	-	820	

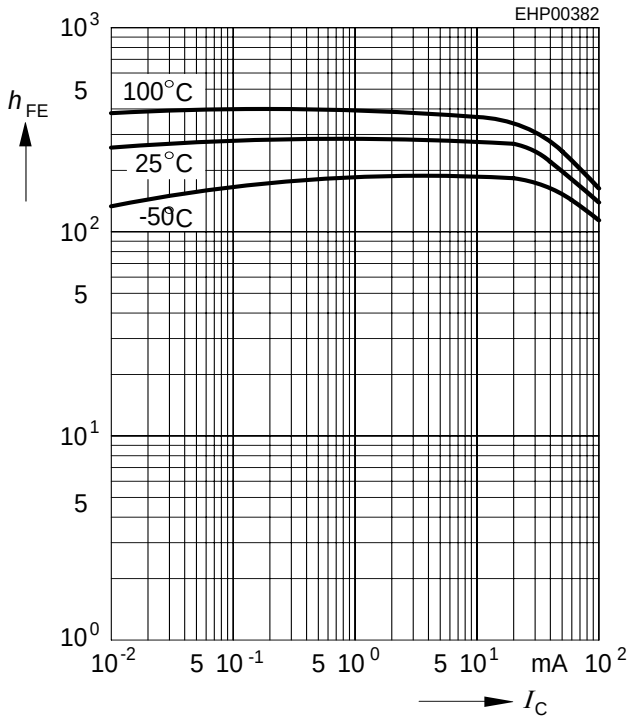
[1]Pulse test: t < 300µs; D < 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency I_C = 20 mA, V_{CE} = 5 V, f = 100 MHz	f_T	-	250	-	MHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz	C_{cb}	-	1.5	-	pF
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz	C_{eb}	-	8	-	
Short-circuit input impedance	h_{11e}				kΩ
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	2.7	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	4.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	8.7	-	
Open-circuit reverse voltage transf. ratio	h_{12e}				10^{-4}
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	1.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	2	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	3	-	
Short-circuit forward current transf. ratio	h_{21e}				-
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	200	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	330	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	600	-	
Open-circuit output admittance	h_{22e}				µS
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	18	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	30	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	60	-	
Noise figure I_C = 0.2 mA, V_{CE} = 5 V, f = 1 kHz, Δf = 200 Hz, R_S = 2 kΩ, BC859, BC850	F	-	1	4	dB
Equivalent noise voltage I_C = 200 mA, V_{CE} = 5 V, R_S = 2 kΩ, f = 10...50 Hz, BC860	V_n	-	-	0.11	µV

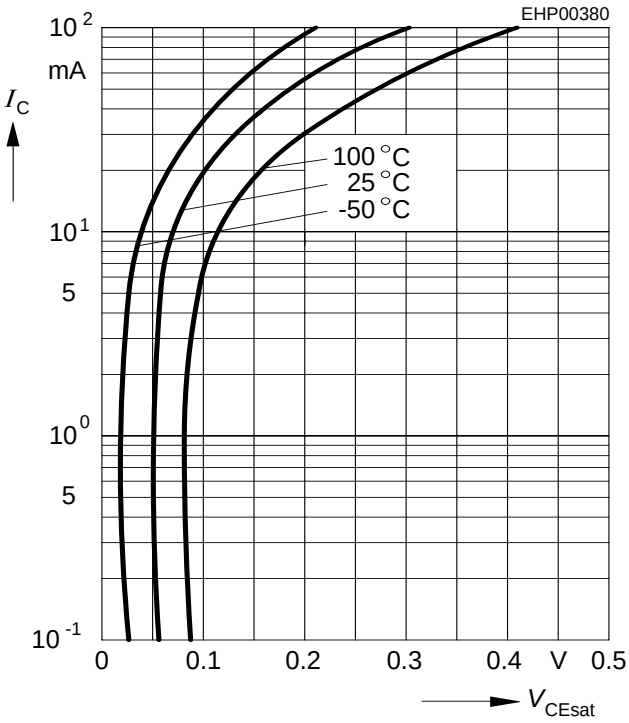
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 1 V



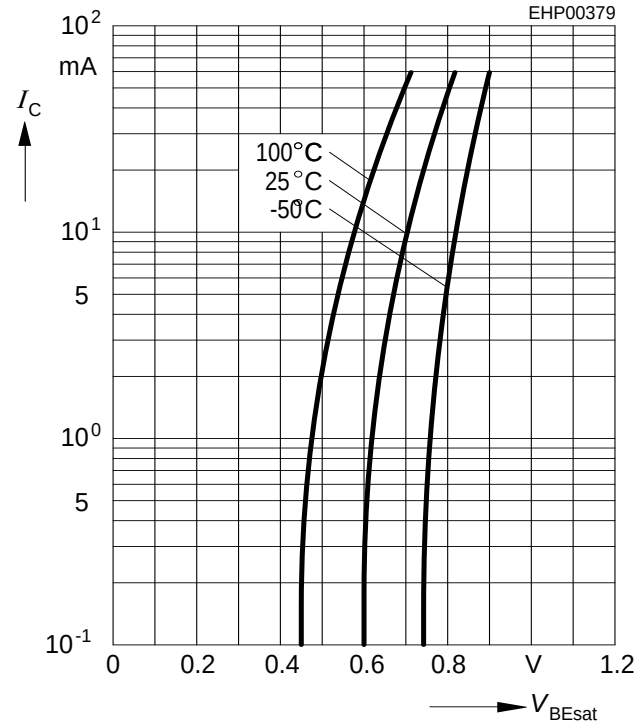
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, h_{FE} = 20



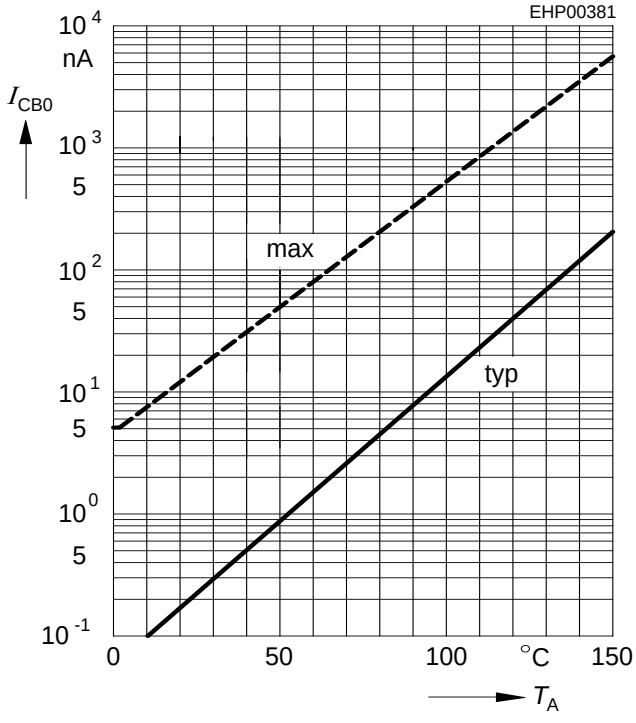
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, h_{FE} = 20



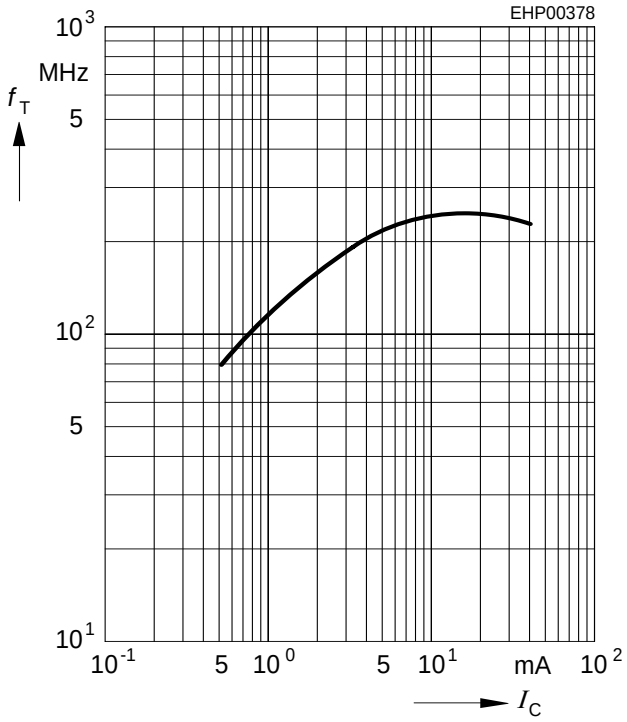
Collector cutoff current $I_{CBO} = f(T_A)$

V_{CBO} = 30 V



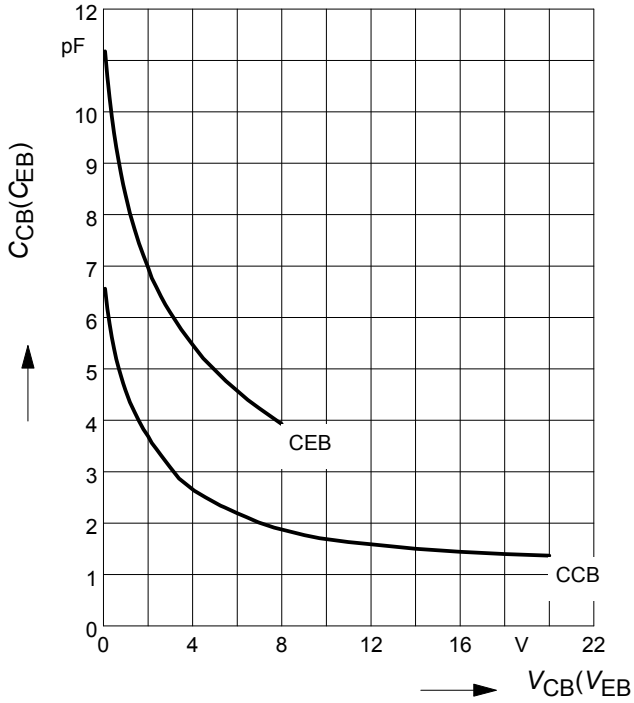
Transition frequency $f_T = f(I_C)$

V_{CE} = 5 V



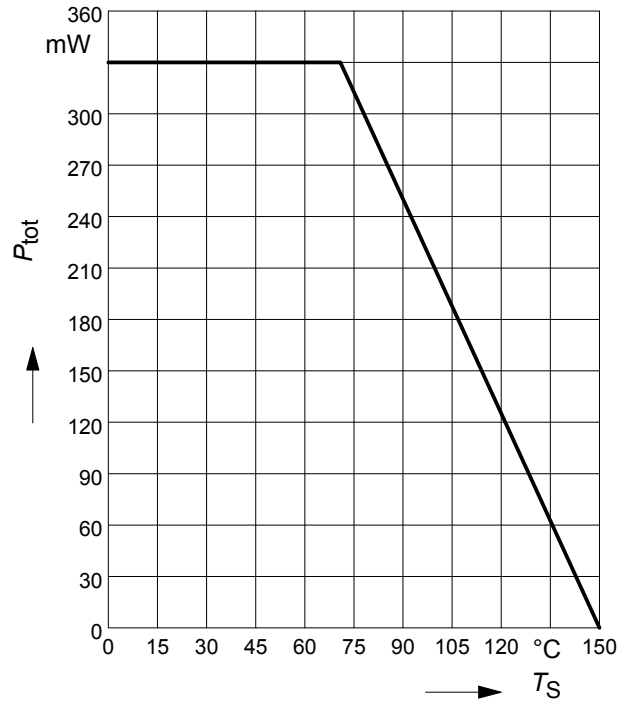
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



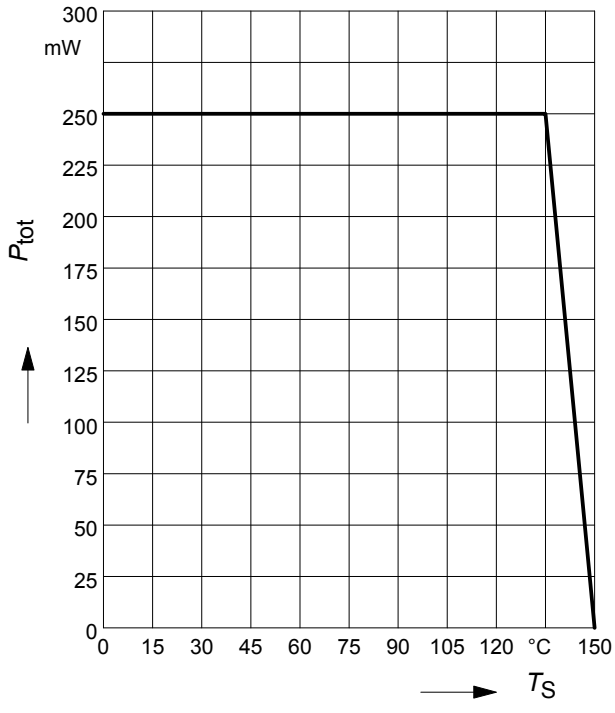
Total power dissipation $P_{tot} = f(T_S)$

BC856-BC860



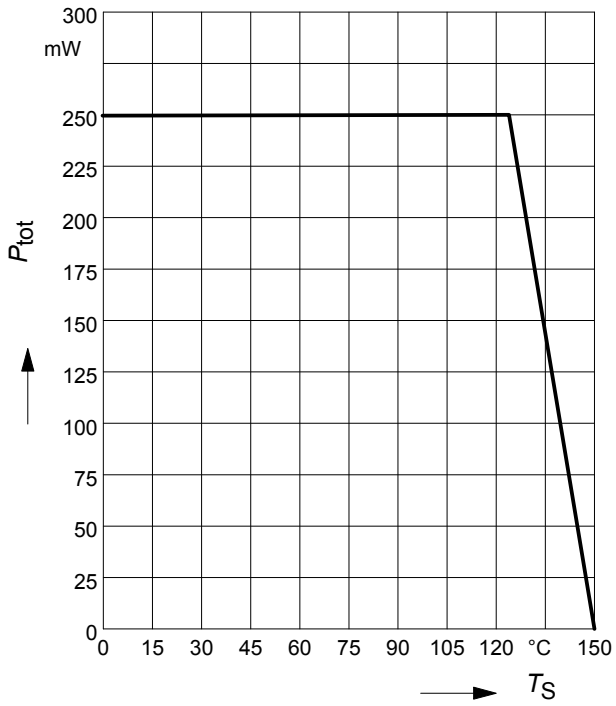
Total power dissipation $P_{tot} = f(T_S)$

BC857BL3



Total power dissipation $P_{tot} = f(T_S)$

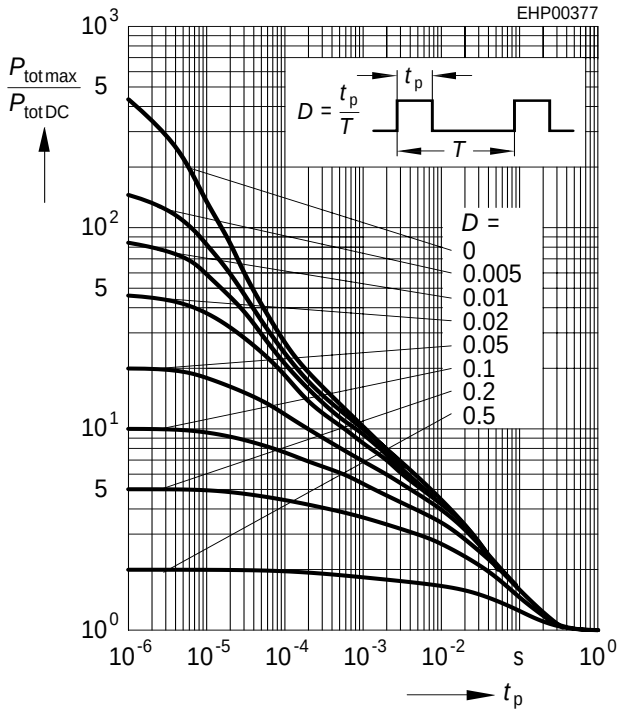
BC857W-BC860W



Permissible Pulse Load

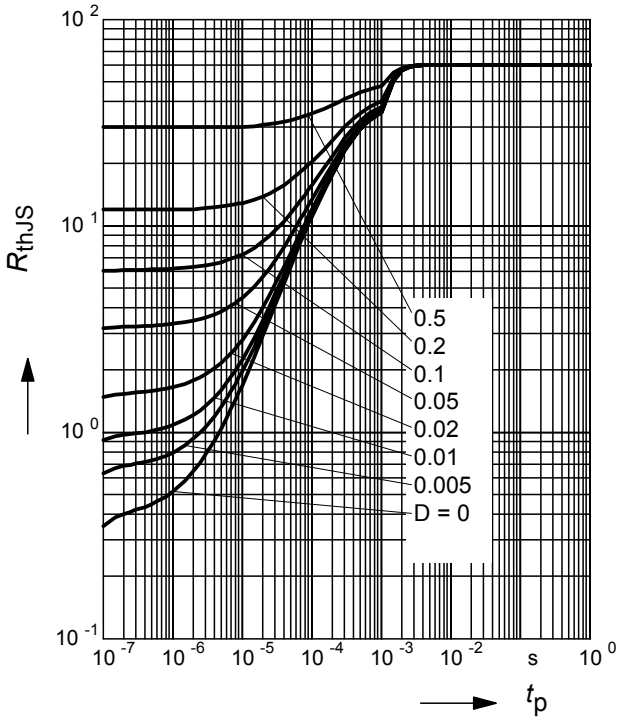
$P_{totmax}/P_{totDC} = f(t_p)$

BC857/W-BC860/W



Permissible Puls Load $R_{thJS} = f(t_p)$

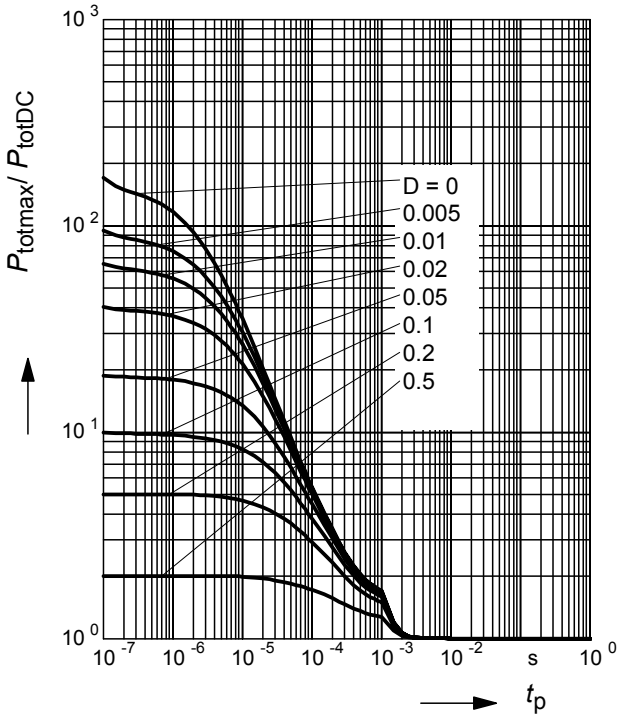
BC857BL3



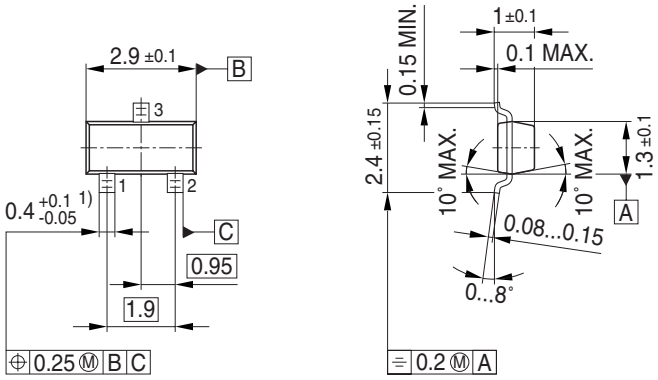
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BC857BL3

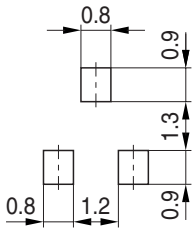


Package Outline

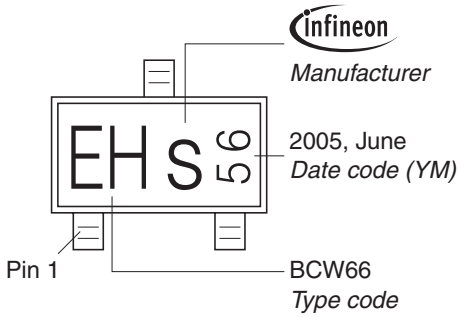


1) Lead width can be 0.6 max. in dambar area

Foot Print

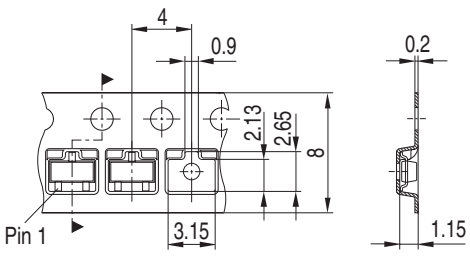


Marking Layout (Example)

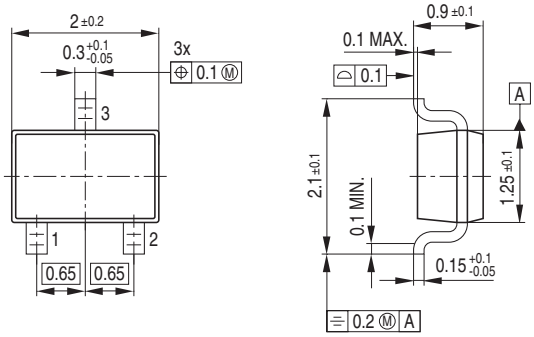


Standard Packing

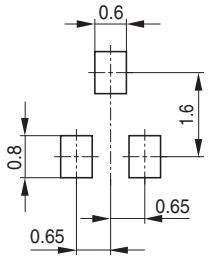
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



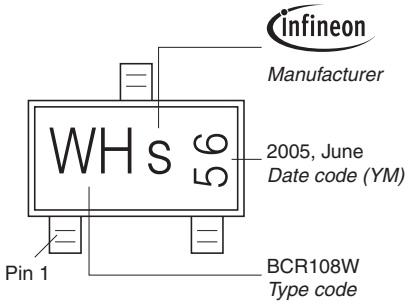
Package Outline



Foot Print

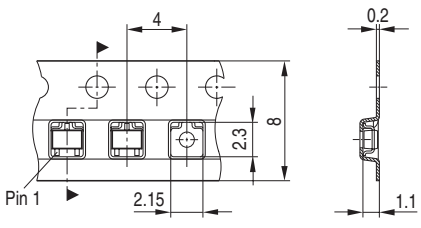


Marking Layout (Example)

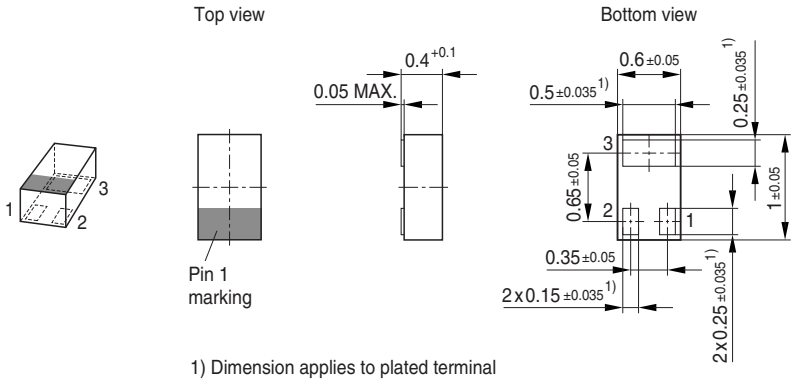


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



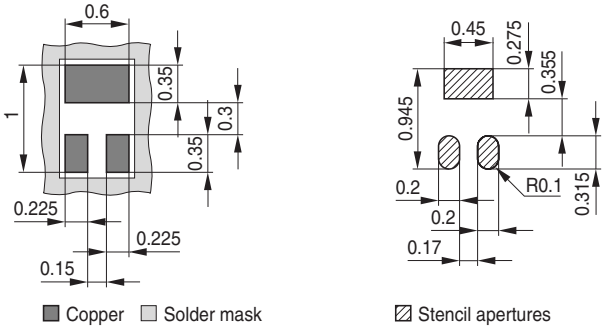
Package Outline



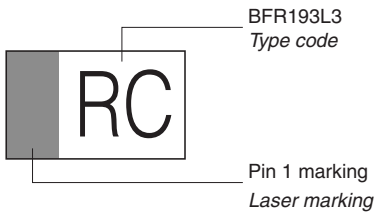
1) Dimension applies to plated terminal

Foot Print

For board assembly information please refer to Infineon website "Packages"

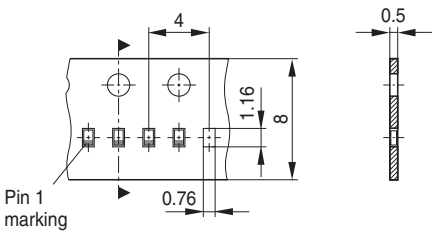


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel

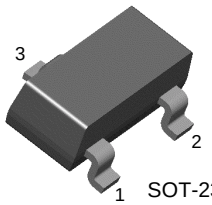


FAIRCHILD
SEMICONDUCTOR®

BC856/857/858/859/860

Switching and Amplifier Applications

- Suitable for automatic insertion in thick and thin-film circuits
- Low Noise: BC859, BC860
- Complement to BC846 ... BC850



SOT-23

1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: BC856	-80	V
	: BC857/860	-50	V
	: BC858/859	-30	V
V_{CEO}	Collector-Emitter Voltage		
	: BC856	-65	V
	: BC857/860	-45	V
	: BC858/859	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current (DC)	-100	mA
P_C	Collector Power Dissipation	310	mW
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-65 ~ 150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
I_{CBO}	Collector Cut-off Current	V_{CB}= -30V, I_E=0			-15	nA
h_{FE}	DC Current Gain	V_{CE}= -5V, I_C= -2mA	110		800	
V_{CE} (sat)	Collector-Emitter Saturation Voltage	I_C= -10mA, I_B= -0.5mA		-90	-300	mV
		I_C= -100mA, I_B= -5mA		-250	-650	mV
V_{BE} (sat)	Base-Emitter Saturation Voltage	I_C= -10mA, I_B= -0.5mA		-700		mV
		I_C= -100mA, I_B= -5mA		-900		mV
V_{BE} (on)	Base-Emitter On Voltage	V_{CE}= -5V, I_C= -2mA	-600	-660	-750	mV
		V_{CE}= -5V, I_C= -10mA			-800	mV
f_T	Current Gain Bandwidth Product	V_{CE}= -5V, I_C= -10mA f=100MHz		150		MHz
C_{ob}	Output Capacitance	V_{CB}= -10V, I_E=0, f=1MHz			6	pF
NF	Noise Figure : BC856/857/858	V_{CE}= -5V, I_C= -200μA		2	10	dB
	: BC859/860	f=1KHz, R_G=2KΩ		1	4	dB
	: BC859	V_{CE}= -5V, I_C= -200μA		1.2	4	dB
	: BC860	R_G=2KΩ, f=30~15000Hz		1.2	2	dB

h_{FE} Classification

Classification	A	B	C
h_{FE}	110 ~ 220	200 ~ 450	420 ~ 800

Marking Code

Type	856A	856B	856C	857A	857B	857C	858A	858B	858C
Mark	9AA	9AB	9AC	9BA	9BB	9BC	9CA	9CB	9CC

Type	859A	859B	859C	860A	860B	860C
Mark	9DA	9DB	9DC	9EA	9EB	9EC

Typical Characteristics

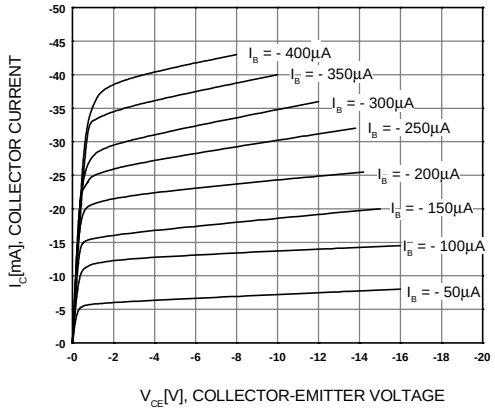


Figure 1. Static Characteristic

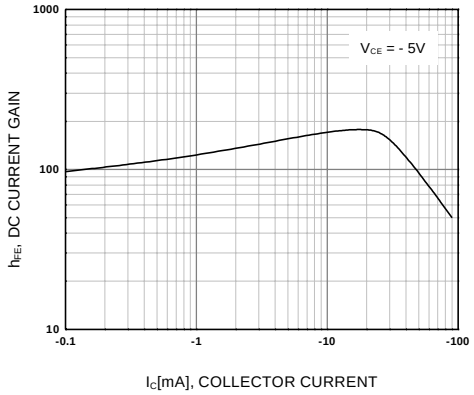


Figure 2. DC current Gain

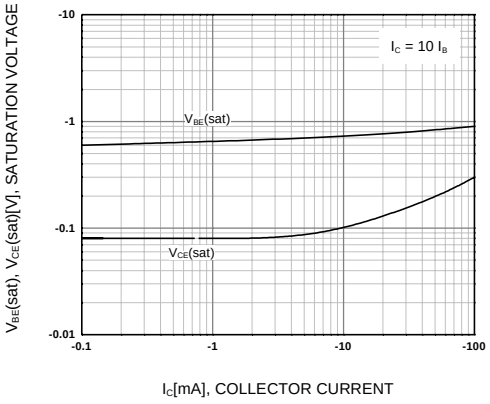


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

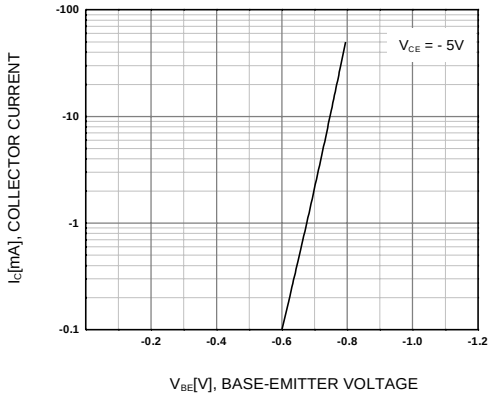


Figure 4. Base-Emitter On Voltage

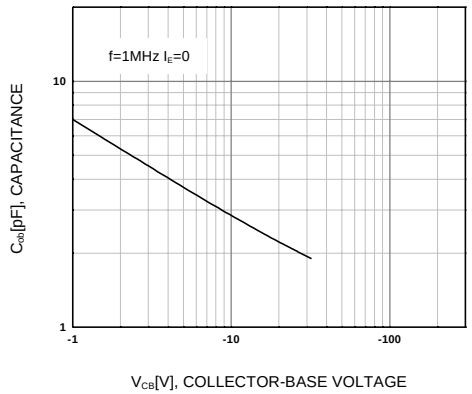


Figure 5. Collector Output Capacitance

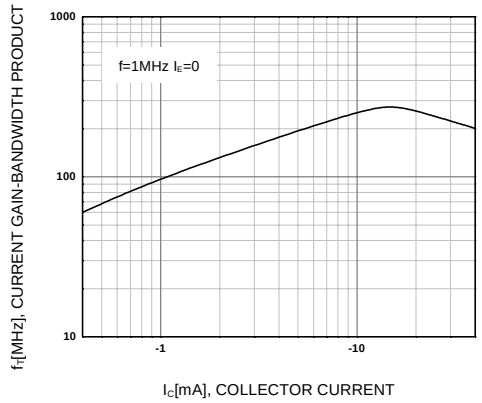
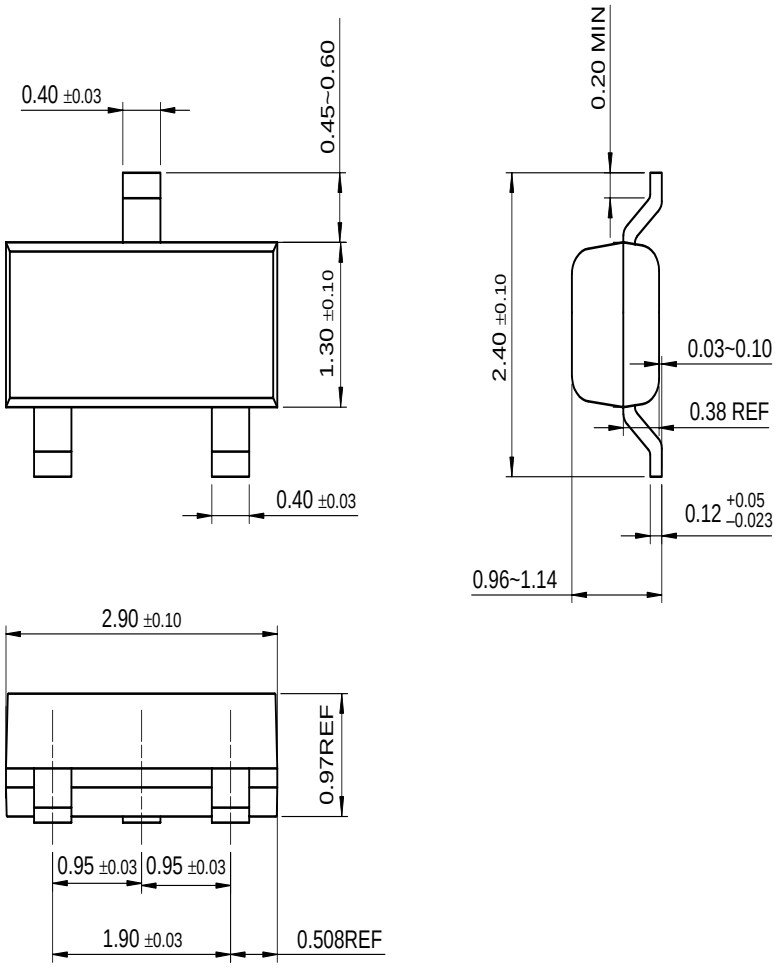


Figure 6. Current Gain Bandwidth Product

Package Dimensions

SOT-23



Dimensions in Millimeters